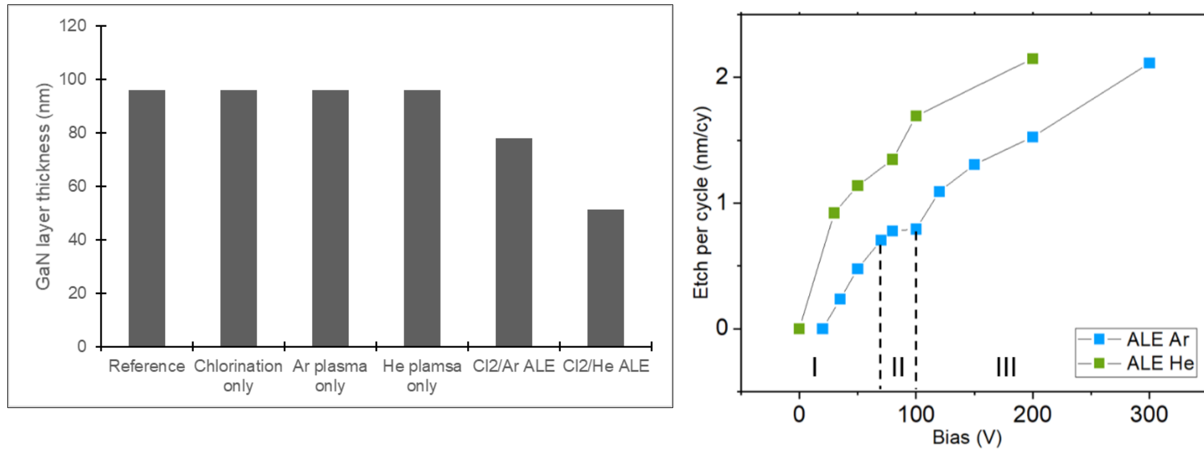

Figure 1 : a) Remaining GaN layer thickness after synergy test at 50V bias after 40 cycles and b) Ideal Window for ALE He & Ar

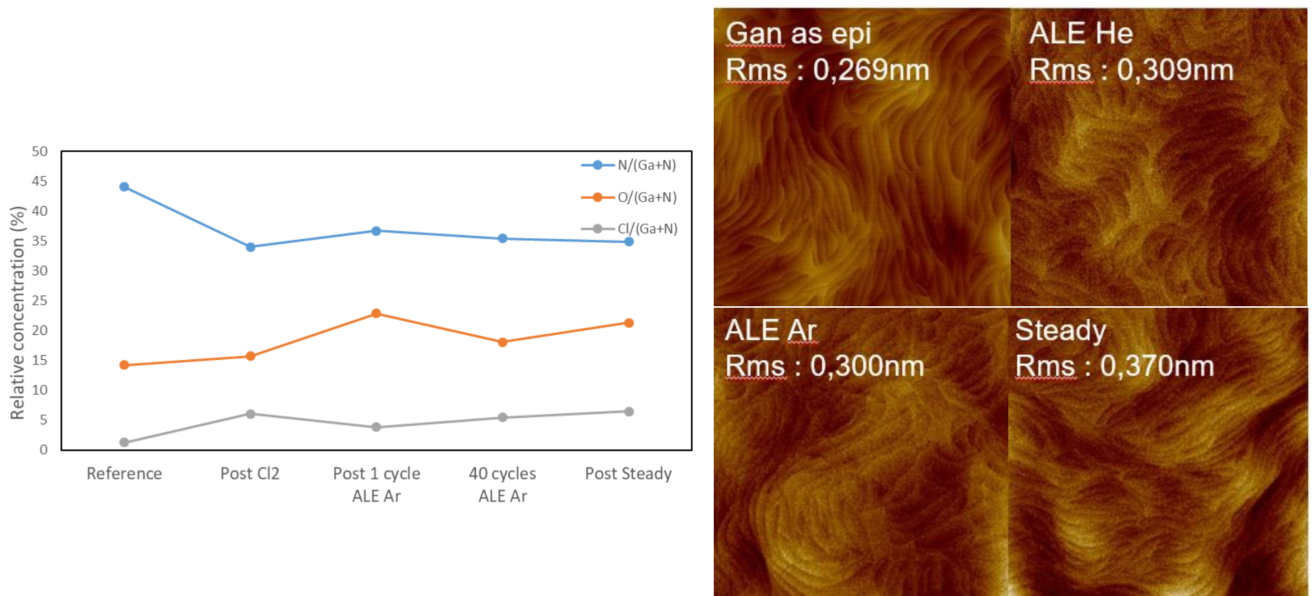

Figure 2 : a) Relative concentration of N, O & Cl (XPS) and b) Roughness measures (AFM), after different etching processes

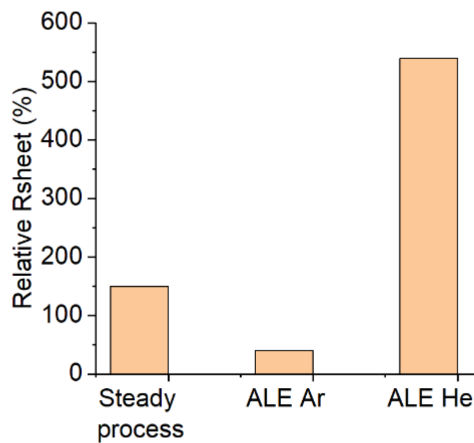

Figure 3 : Relative Rsheet (%) for different processes